

MOSFETs Silicon N-channel MOS (U-MOSIX-H)

# TPH1R204PL

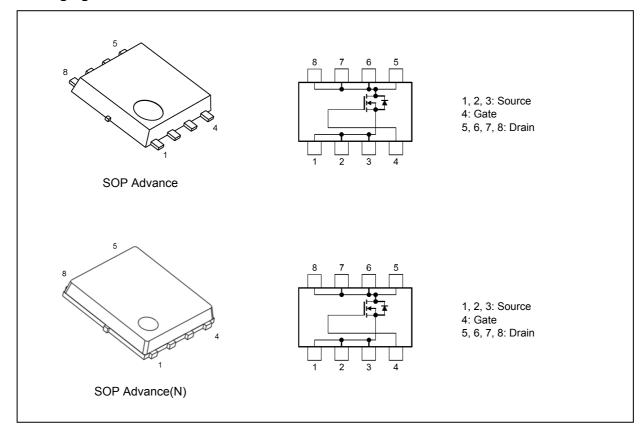
### 1. Applications

- · High-Efficiency DC-DC Converters
- Switching Voltage Regulators

#### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 17 \text{ nC (typ.)}$
- (3) Small output charge:  $Q_{oss} = 56 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 1.0 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (5) Low leakage current:  $I_{\rm DSS}$  = 10  $\mu A$  (max) (V\_{DS} = 40 V)
- (6) Enhancement mode:  $V_{th} = 1.4 \text{ to } 2.4 \text{ V } (V_{DS} = 10 \text{ V}, I_D = 0.5 \text{ mA})$

#### 3. Packaging and Internal Circuit



The package can be selected according to your preference. For details, please contact your TOSHIBA sales representative.

Start of commercial production



### 4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			$V_{DSS}$	40	V
Gate-source voltage			$V_{GSS}$	±20	
Drain current (DC)	(T <sub>c</sub> = 25 °C)	(Note 1), (Note 2)	Ι <sub>D</sub>	150	Α
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	$I_D$	246	Α
Drain current (pulsed)	(t = 100 μs)	(Note 1)	I <sub>DP</sub>	500	Α
Power dissipation	$(T_c = 25 ^{\circ}C)$		$P_D$	132	W
Power dissipation		(Note 3)	$P_{D}$	3	W
Power dissipation		(Note 4)	$P_D$	0.96	W
Single-pulse avalanche energy		(Note 5)	E <sub>AS</sub>	127	mJ
Single-pulse avalanche current		(Note 5)	I <sub>AS</sub>	120	Α
Channel temperature			T <sub>ch</sub>	175	°C
Storage temperature			T <sub>stg</sub>	-55 to 175	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics				Max	Unit
Channel-to-case thermal resistance	(T <sub>c</sub> = 25 °C)		R <sub>th(ch-c)</sub>	1.13	°C/W
Channel-to-ambient thermal resistance	(T <sub>a</sub> = 25 °C)	(Note 3)	R <sub>th(ch-a)</sub>	50	
Channel-to-ambient thermal resistance	(T <sub>a</sub> = 25 °C)	(Note 4)	R <sub>th(ch-a)</sub>	156	

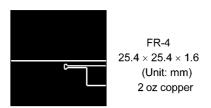
Note 1: Ensure that the channel temperature does not exceed 175 °C.

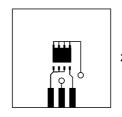
Note 2: Limited by package limit. Silicon chip capability is 246 A. ( $T_c$  = 25 °C)

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5:  $V_{DD}$  = 32 V,  $T_{ch}$  = 25 °C (initial), L = 0.0068 mH,  $I_{AS}$  = 120 A





FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2 oz copper

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

# 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	μΑ
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V	_		10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	40			V
	V <sub>(BR)DSX</sub>	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	25	_	_	
Gate threshold voltage	$V_{th}$	$V_{DS}$ = 10 V, $I_{D}$ = 0.5 mA	1.4		2.4	
Drain-source on-resistance	R <sub>DS(ON)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 50 \text{ A}$	_	1.5	2.1	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 50 A	_	1.0	1.24	

# 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	5500	7200	pF
Reverse transfer capacitance	$C_{rss}$		_	93		
Output capacitance	C <sub>oss</sub>		_	1300		
Gate resistance	r <sub>g</sub>	_	_	0.6	1.1	Ω
Switching time (rise time)	t <sub>r</sub>	See Fig. 6.2.1	_	13		ns
Switching time (turn-on time)	t <sub>on</sub>		_	33		
Switching time (fall time)	t <sub>f</sub>		_	10	_	
Switching time (turn-off time)	t <sub>off</sub>		_	58	_	

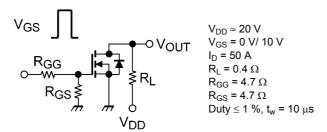


Fig. 6.2.1 Switching Time Test Circuit

# 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	$Q_g$	$V_{DD} \approx 20 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$	-	74	_	nC
gate-drain)		$V_{DD} \approx 20 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 50 \text{ A}$		34	_	
Gate-source charge 1	Q <sub>gs1</sub>	$V_{DD} \approx 20 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$		16	_	
Gate-drain charge	$Q_{gd}$		_	17	_	
Gate switch charge	$Q_{SW}$			17	_	
Output charge	Q <sub>oss</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V	_	56	_	



# 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 6)	I <sub>DRP</sub> (t = 100 μs)	_	_	_	500	Α
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 150 A, V <sub>GS</sub> = 0 V		_	-1.2	V
Reverse recovery time	t <sub>rr</sub>	$V_R = 20 \text{ V}, I_{DR} = 37.5 \text{ A}, V_{GS} = 0 \text{ V}, -dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$	-	46	-	ns
Reverse recovery charge	Q <sub>rr</sub>	$V_R = 20 \text{ V}, I_{DR} = 37.5 \text{ A}, V_{GS} = 0 \text{ V}, -dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$		46		nC

Note 6: Ensure that the channel temperature does not exceed 175 °C.

# 7. Marking

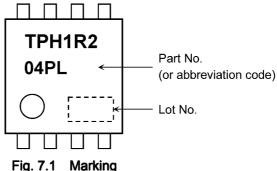


Fig. 7.1 Marking



### 8. Characteristics Curves (Note)

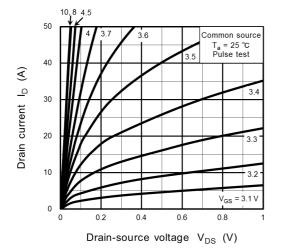


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

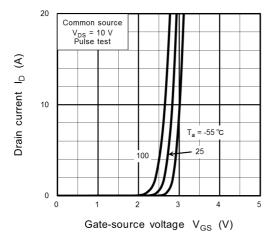


Fig. 8.3 I<sub>D</sub> - V<sub>GS</sub>

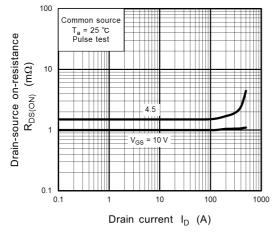


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

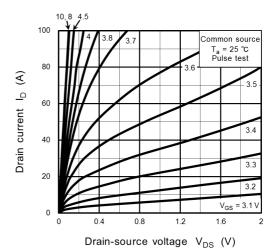


Fig. 8.2  $I_D - V_{DS}$ 

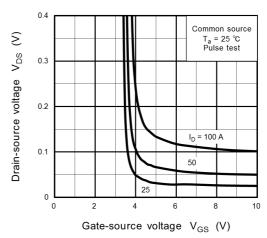


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

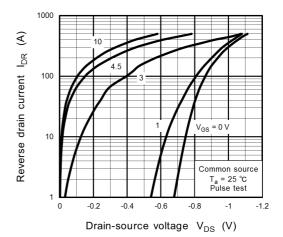


Fig. 8.6 IDR - VDS



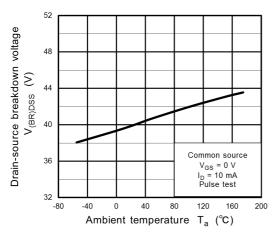


Fig. 8.7 V<sub>(BR)DSS</sub> - T<sub>a</sub>

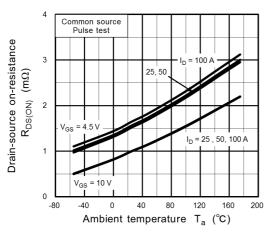


Fig. 8.9 R<sub>DS(ON)</sub> - T<sub>a</sub>

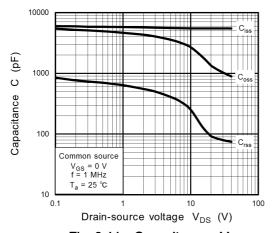


Fig. 8.11 Capacitance - V<sub>DS</sub>

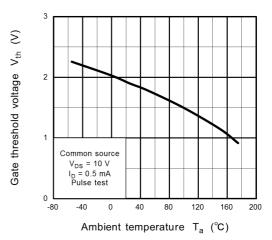


Fig. 8.8 V<sub>th</sub> - T<sub>a</sub>

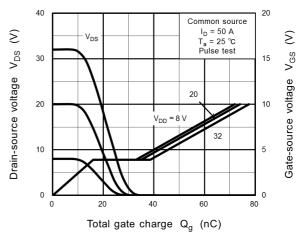


Fig. 8.10 Dynamic Input/Output Characteristics

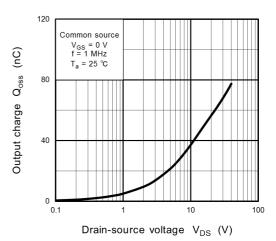


Fig. 8.12 Qoss - VDS



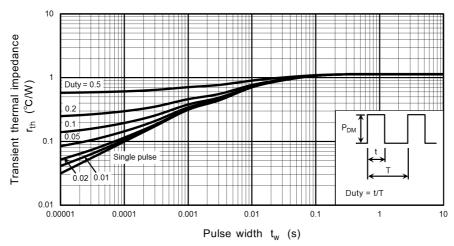


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

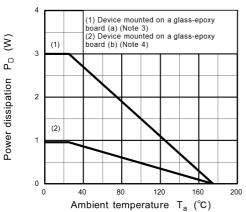


Fig. 8.14 P<sub>D</sub> - T<sub>a</sub> (Guaranteed Maximum)

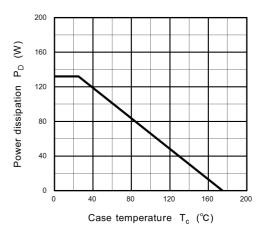


Fig. 8.15 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

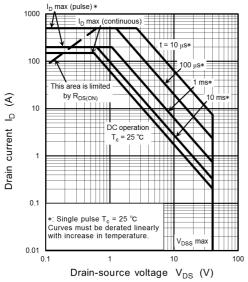


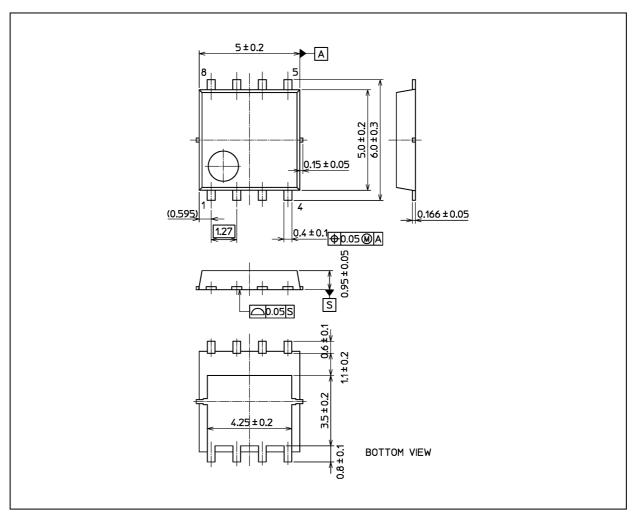
Fig. 8.16 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



# **Package Dimensions**

Unit: mm



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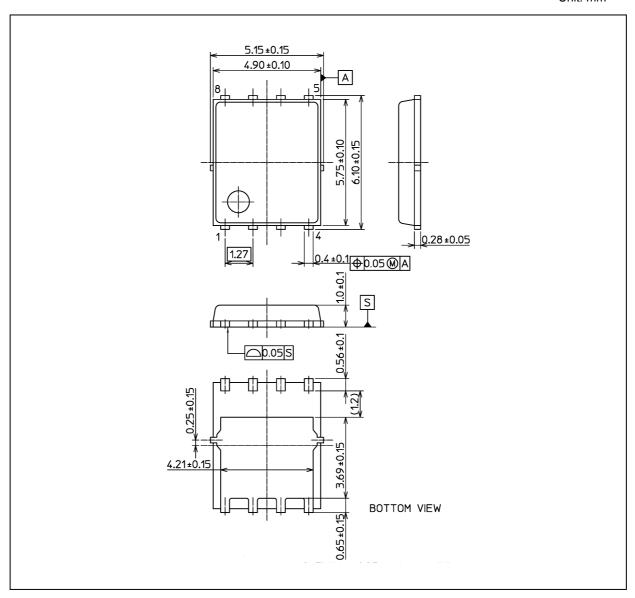
Weight: 0.079 g (typ.)

	Package Name(s)
TOSHIBA: 2-5Q1S	
Nickname: SOP Advance	



# **Package Dimensions**

Unit: mm



The package can be selected according to your preference. For details, please contact your TOSHIBA sales representative.

Weight: 0.105 g (typ.)

Package Name(s)
TOSHIBA: 2-5W1A
Nickname: SOP Advance(N)



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